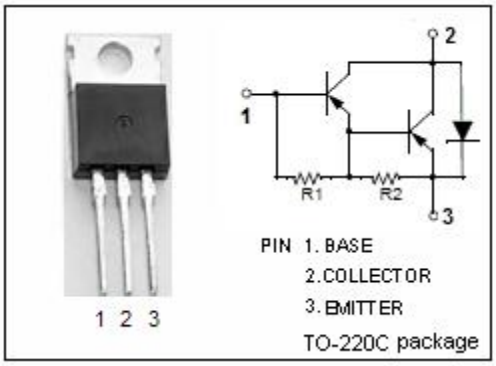
isc Silicon PNP Darlington Power Transistor BD702



DESCRIPTION

- Collector–Emitter Sustaining Voltage—
  : $V_{CEO(SUS)}$ = -100V(Min.)
- DC Current Gain—
  : h_{FE} = 750(Min) @ I_C= -3A
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

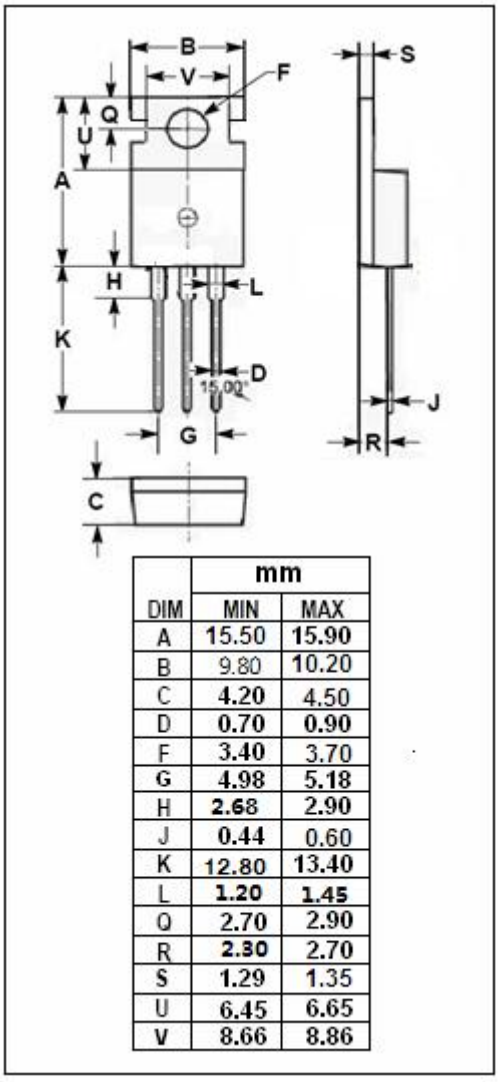
- Designed for output devices in complementary general-purpose amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-8	A
I_B	Base Current	-0.1	A
P_C	Collector Power Dissipation T_C=25℃	70	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.79	℃/W



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -30mA; I_B= 0	-100		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -3A ,I_B= -12mA		-2.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -3A; V_{CE}= -3V		-2.5	V
I_{CEO}	Collector Cutoff Current	V_{CE}= -100V; I_B= 0		-0.5	mA
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V; I_E= 0		-0.2	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0		-2.0	mA
h_{FE}	DC Current Gain	I_C= -3A ; V_{CE}= -3V	750		